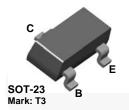


March 2014

BSS63 PNP General-Purpose Amplifier

Description

This device is designed for general-purpose amplifier and switch applications requiring high voltages. Sourced from process 74.



Ordering Information

Part Number	Marking	Package	Packing Method
BSS63	Т3	SOT-23 3L	Tape and Reel

Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-Emitter Voltage	-100	V
V _{CBO}	Collector-Base Voltage -1		V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current - Continuous	-200	mA
T_{J} , T_{STG}	Junction and Storage Temperature Range -55 to +150		°C

Notes

- 1. These ratings are based on a maximum junction temperature of 150°C.
- These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

1

Thermal Characteristics(3)

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Max.	Unit
В	Total Device Dissipation	350	mW
P _D	Derate Above T _A = 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

Note:

3. Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

Electrical Characteristics

Values are at $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_C = -100 \mu\text{A}, I_B = 0$	-100		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = -10 \mu A, I_E = 0$	-110		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = -1.0 \mu\text{A}, I_C = 0$	-6.0		V
I _{CBO}	Collector Cut-Off Current	$V_{CB} = -90 \text{ V}, I_{E} = 0$		-100	nA
		$V_{CB} = -90 \text{ V}, I_E = 0,$ $T_A = 150^{\circ}\text{C}$		-50	μА
I _{EBO}	Emitter Cut-Off Current	$V_{EB} = -6.0 \text{ V}, I_{C} = 0$		-200	nA
h _{FE}	DC Current Gain	$I_C = -10 \text{ mA}, V_{CE} = -1.0 \text{ V}$	30		
		$I_C = -25 \text{ mA}, V_{CE} = -1.0 \text{ V}$	30		
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = -25 \text{ mA}, I_B = -2.5 \text{ mA}$		-0.25	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = -25 \text{ mA}, I_B = -2.5 \text{ mA}$		-0.9	V
f _T	Current Gain - Bandwidth Product	$I_C = 25 \text{ mA}, V_{CE} = -5.0 \text{ V},$ f = 35 MHz	50		MHz

Typical Performance Characteristics

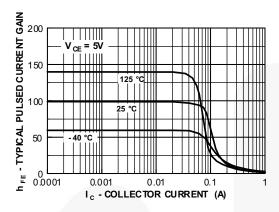


Figure 1. Typical Pulsed Current Gain vs. Collector Current

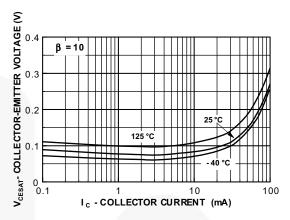


Figure 2. Collector-Emitter Saturation Voltage vs. Collector Current

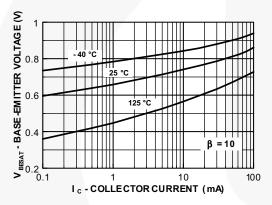


Figure 3. Base-Emitter Saturation Voltage vs. Collector Current

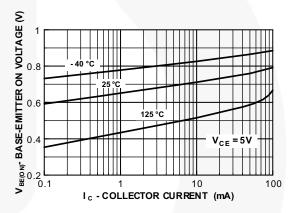


Figure 4. Base-Emitter On Voltage vs. Collector Current

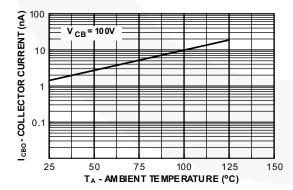


Figure 5. Collector Cut-Off Current vs.
Ambient Temperature

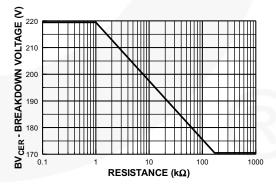


Figure 6. Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base

Typical Performance Characteristics (Continued)

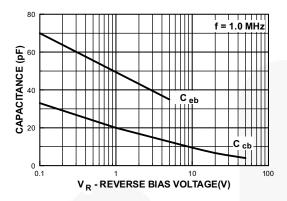


Figure 7. Input and Output Capacitance vs. Reverse Voltage

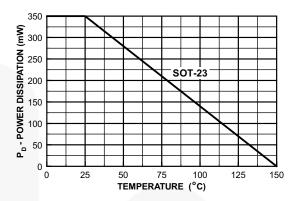


Figure 8. Power Dissipation vs. Ambient Temperature

Physical Dimensions

0.95 2.92±0.20 3 1.40 1.30^{+0.20}_{-0.15} 2.20 0.60 0.37 (0.29) -0.95 ⊕ 0.20M A B 1.00 1.90 1.90 LAND PATTERN RECOMMENDATION 1.20 MAX SEE DETAIL A (0.93)0.10 ○ 0.10 M C C 2.40±0.30 NOTES: UNLESS OTHERWISE SPECIFIED **GAGE PLANE** A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H. B) ALL DIMENSIONS ARE IN MILLIMETERS. 0.23 0.08 C) DIMENSIONS ARE INCLUSIVE OF BURRS, 0.25 MOLD FLASH AND TIE BAR EXTRUSIONS. D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 1994. 0.20 MIN E) DRAWING FILE NAME: MA03DREV10 SEATING

SOT-23

Figure 9. 3-LEAD, SOT23, JEDEC TO-236, LOW PROFILE (ACTIVE)

PLANE

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DETAIL A





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Definition of Terms			
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